

YAO-3950

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yoshihisa Nagano et al.

: Art Unit: 2815

Serial No.: 09/103,873

: Examiner: J. Diaz

Filed: June 24, 1998

: **RESPONSE UNDER
1.116**

For: SEMICONDUCTOR DEVICE AND
METHOD FOR FABRICATING THE SAME

: **EXPEDITED
PROCEDURE**

PRELIMINARY AMENDMENT AND REQUEST FOR
EXTENSION OF TIME

Assistant Commissioner for Patents
Washington, DC 20231

S I R :

Prior to examination, please amend the above-identified application
as follows:

IN THE DRAWINGS:

Please amend Figure 7 as indicated in red on the enclosed copy of
Figure 7.

CLAIMS:

✓
Please cancel claim 28.

✓
Please add claims 29-31:

1 29. (Newly Added) The semiconductor device of claim 1 wherein
2 the second interlayer insulating film provides substantially flat step coverage of the
3 first interconnect and the first interlayer insulating film.

1 30. (Newly Added) The semiconductor device of claim 1 wherein
2 the dielectric film includes a remnant polarization of approximately $10 \mu\text{C}/\text{cm}^2$.

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T. Flowers

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